

Ultrafast Rectifier

30 A, 600 V

RURG3060CC-F085

Description

The RURG3060-F085 is an dual ultrafast diode with soft recovery characteristics ($t_{rr} < 80$ ns). It has low forward voltage drop and is silicon nitride passivated ionimplanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristic minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Features

- High Speed Switching ($t_{rr} = 60$ ns (Typ.) @ $I_F = 30$ A)
- Low Forward Voltage ($V_F = 1.5$ V (Max) @ $I_F = 30$ A)
- Avalanche Energy Rated
- AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

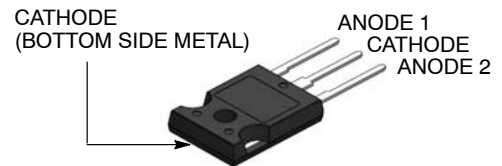
Applications

- Automotive DC/DC Converter
- Automotive On Board Charger
- Switching Power Supply
- Power Switching Circuits

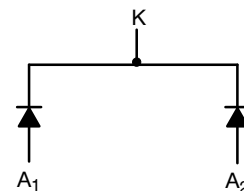


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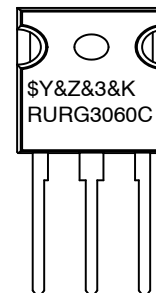
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TO-247-3LD
CASE 340CK



MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
RURG3060C	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

RURG3060CC-F085

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	600	V
Working Peak Reverse Voltage	V _{RWM}	600	V
DC Blocking Voltage	V _R	600	V
Average Rectified Forward Current (T _C = 25°C)	I _{F(AV)}	30	A
Non-repetitive Peak Surge Current (Halfwave 1 Phase 50 Hz)	I _{FSM}	90	A
Avalanche Energy (1 A, 40 mH)	E _{AVL}	20	mJ
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Tube	Quantity
RURG3060CC-F085	RURG3060C	TO-247	-	30

THERMAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Max	Unit
Maximum Thermal Resistance, Junction to Case (Single Anode)	R _{θJC}	1	°C/W
Maximum Thermal Resistance, Junction to Ambient	R _{θJA}	45	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Instantaneous Reverse Current	I _R	V _R = 600 V	T _C = 25°C	-	-	250	μA
			T _C = 175°C	-	-	1.0	mA
Instantaneous Forward Voltage	V _{FM} (Note 1)	I _F = 30 A	T _C = 25°C	-	1.26	1.5	V
			T _C = 175°C	-	1.06	1.3	V
Reverse Recovery Time	t _{rr} (Note 2)	I _F = 1 A, di/dt = 100 A/μs, V _{CC} = 390 V	T _C = 25°C	-	35	55	ns
			T _C = 25°C	-	60	80	ns
			T _C = 175°C	-	231	-	ns
Reverse Recovery Time	t _a	I _F = 30 A, di/dt = 100 A/μs, V _{CC} = 390 V	T _C = 25°C	-	31	-	ns
	t _b			-	29	-	ns
Reverse Recovery Charge	Q _{rr}			-	92	-	nC
Avalanche Energy	E _{AVL}	I _{AV} = 1.0 A, L = 40 mH		20	-	-	mJ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Test Pulse Width = 300 μs, Duty Cycle = 3%
2. Guaranteed by design.

TEST CIRCUIT AND WAVEFORMS

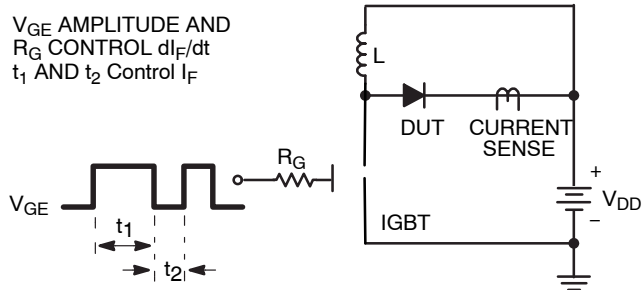


Figure 1. t_{rr} Test Circuit

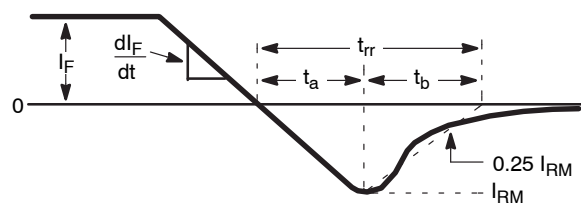


Figure 2. t_{rr} Waveforms and Definitions

$I_{MAX} = 1 \text{ A}$
 $L = 40 \text{ mH}$
 $R < 0.1 \Omega$
 $E_{AVL} = 1/2 L I^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
 $Q_1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)})$

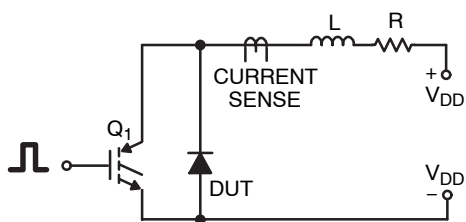


Figure 3. Avalanche Energy Test Circuit

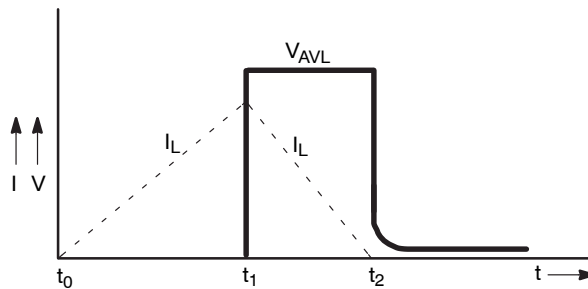


Figure 4. Avalanche Current and Voltage Waveforms

TYPICAL PERFORMANCE CHARACTERISTICS (Single Anode)

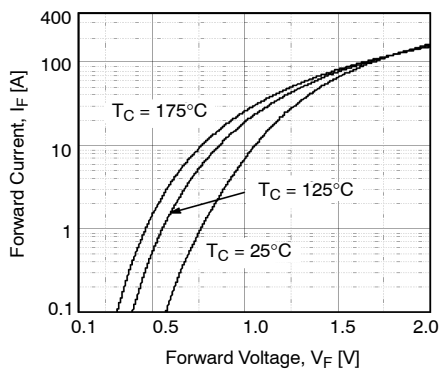


Figure 5. Typical Forward Voltage Drop vs. Forward Current

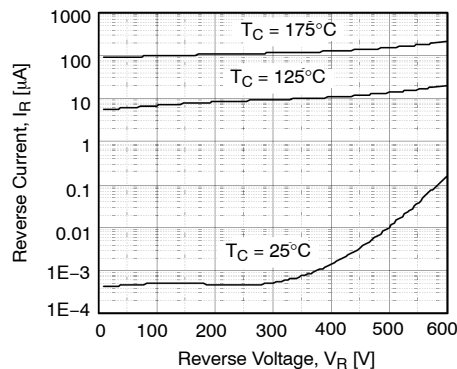


Figure 6. Typical Reverse Current vs. Reverse Voltage

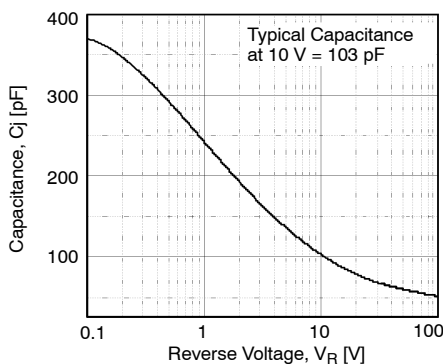


Figure 7. Typical Junction Capacitance

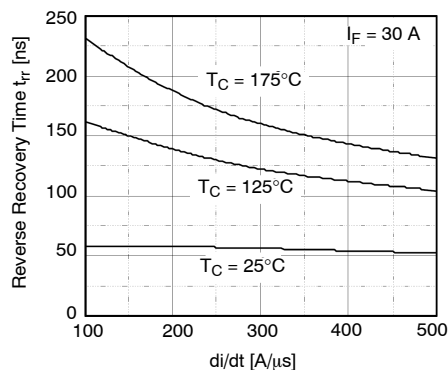


Figure 8. Typical Reverse Recovery Time vs. di/dt

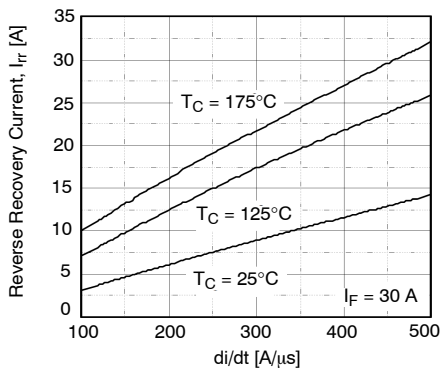


Figure 9. Typical Reverse Recovery Current vs. di/dt

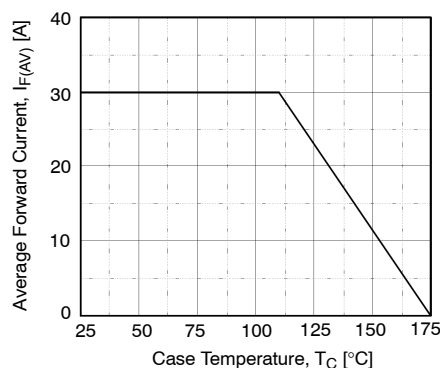


Figure 10. Forward Current Derating Curve

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

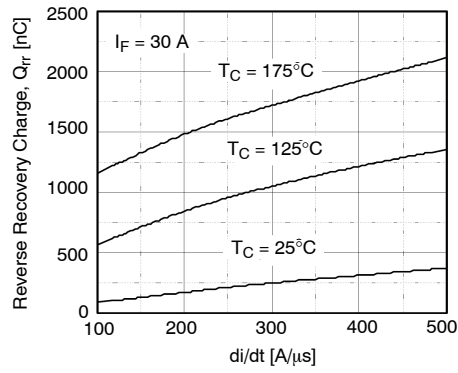


Figure 11. Reverse Recovery Charge

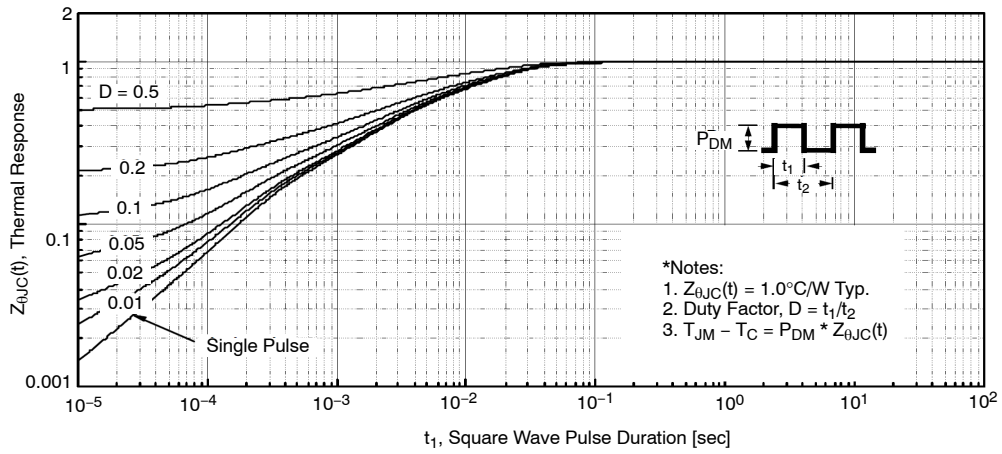
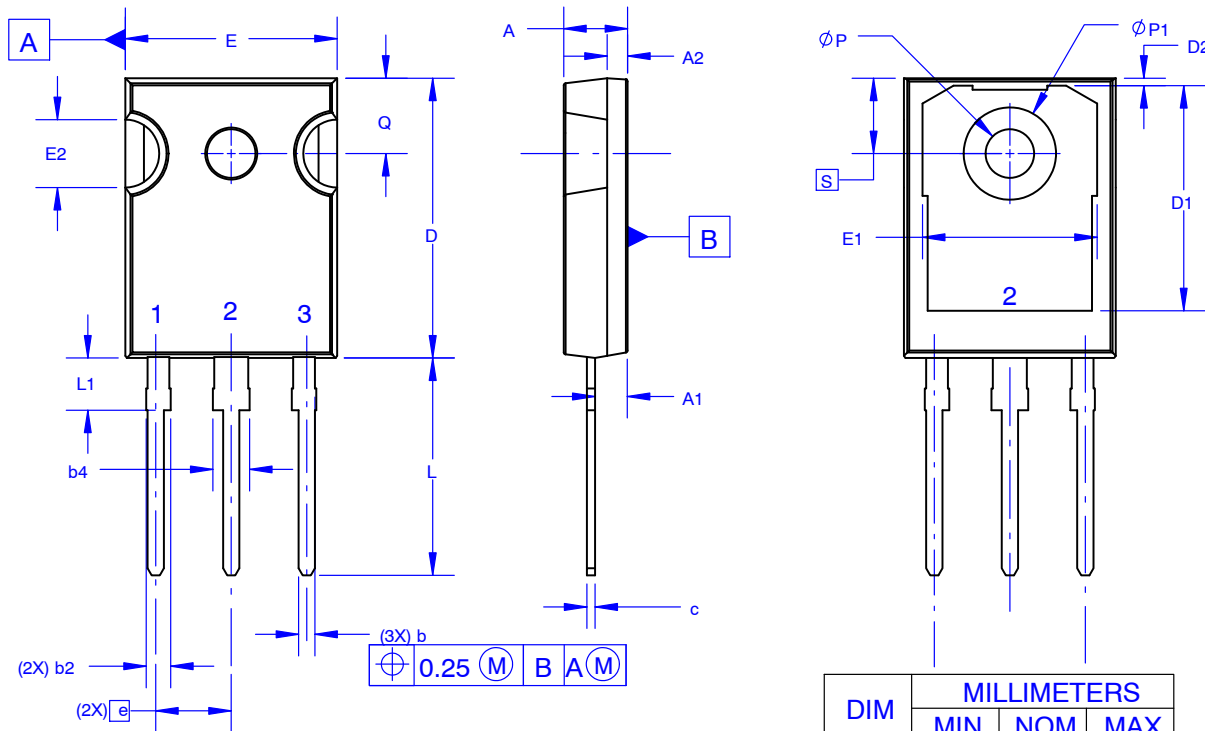


Figure 12. Transient Thermal Response Curve



TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

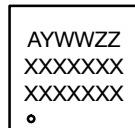
DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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DESCRIPTION:	TO-247-3LD SHORT LEAD	PAGE 1 OF 1

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